

**AMENDMENTS TO THE CLAIM**

Please amend claims 6 and 7, to read as follows:

1. (Original) A silicon semiconductor substrate comprising:  
a {110} plane or a plane inclined from a {110} plane as a main surface of the substrate; and  
steps arranged at an atomic level along a  $\langle 110 \rangle$  orientation on the main surface.
2. (Original) The silicon semiconductor substrate according to claim 1, wherein the plane inclined from the {110} plane is a plane inclined from the {110} plane toward a  $\langle 100 \rangle$  orientation.
3. (Original) The silicon semiconductor substrate according to claim 2, wherein a silicon single crystal thin film is formed by means of an epitaxial growth method on the surface of the silicon semiconductor substrate having the plane inclined from the {110} plane as the main surface.
4. (Original) The silicon semiconductor substrate according to claim 2, wherein the silicon semiconductor substrate having the plane inclined from the {110} plane toward the  $\langle 100 \rangle$  orientation as the main surface is subjected to heat treatment in a hydrogen gas atmosphere, an argon gas atmosphere or an atmosphere of a mixture thereof.
5. (Original) A silicon semiconductor substrate having a plane inclined from a {100} plane toward a  $\langle 100 \rangle$  orientation as a main surface, the surface thereof being mirror polished.
6. (Currently amended) The silicon semiconductor substrate according to ~~any of claims 2 to 5~~ claim 2, wherein an inclination angle of the silicon semiconductor substrate having the plane inclined from the {110} plane toward the  $\langle 100 \rangle$  orientation as the main surface is 0 degree or more and less than 8 degrees.

7. (Currently amended) The silicon semiconductor substrate according to ~~any of claims 1 to 6~~claim 2, wherein an orientation flat or a notch is formed in the  $\langle 110 \rangle$  orientation.

8. (Original) A method for manufacturing a silicon semiconductor substrate, which is the silicon semiconductor substrate according to claim 2, comprising the steps of:

preparing a silicon semiconductor substrate having a plane inclined from a  $\{110\}$  plane toward a  $\langle 100 \rangle$  orientation as a main surface; and

growing a silicon single crystal thin film by means of an epitaxial growth method on the main surface.

9. (Original) A manufacturing method for a silicon semiconductor substrate, which is the silicon semiconductor substrate according to claim 2, comprising steps of:

preparing a silicon semiconductor substrate having a plane inclined from a  $\{110\}$  plane toward a  $\langle 100 \rangle$  orientation as a main surface; and

heat treating the silicon semiconductor substrate in an atmosphere of hydrogen, argon or a mixture thereof.